



TRANSISTORS, MATCHED DUAL, PNP

BASED ON TYPE 2N3810

ESCC Detail Specification No. 5207/005

Issue 5	May 2017
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(Refer to <https://escies.org> for ESCC DCR content)

DCR No.	CHANGE DESCRIPTION
1077 , 1079	Specification upissued to incorporate changes per DCR.

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1 GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. [5000](#)

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. [21300](#) shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 The ESCC Component Number

The ESCC Component Number shall be constituted as follows:

Example: 520700501R

- Detail Specification Reference: 5207005
- Component Type Variant Number: 01 (as required)
- Total Dose Radiation Level Letter: R (as required)

1.4.2 Component Type Variants

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Lead/Terminal Material and/or Finish	Weight max g	Total Dose Radiation Level Letter
01	2N3810	TO-78	D2	0.95	R [100krad(Si)]
02	2N3810	TO-78	D3 or D4	0.95	R [100krad(Si)]
05	2N3810	TO-78	D7	0.95	R [100krad(Si)]
07	2N3810	CCP	2	0.2	R [100krad(Si)]
09	2N3810	CCP	4	0.2	R [100krad(Si)]
10	2N3810	FP	G2	0.7	R [100krad(Si)]
11	2N3810	FP	G4	0.7	R [100krad(Si)]

The lead/terminal material and/or finish shall be in accordance with the requirements of ESCC Basic Specification No. [23500](#).

Total dose radiation level letters are defined in ESCC Basic Specification No. [22900](#). If an alternative radiation test level is specified in the Purchase Order, the letter shall be changed accordingly.

1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

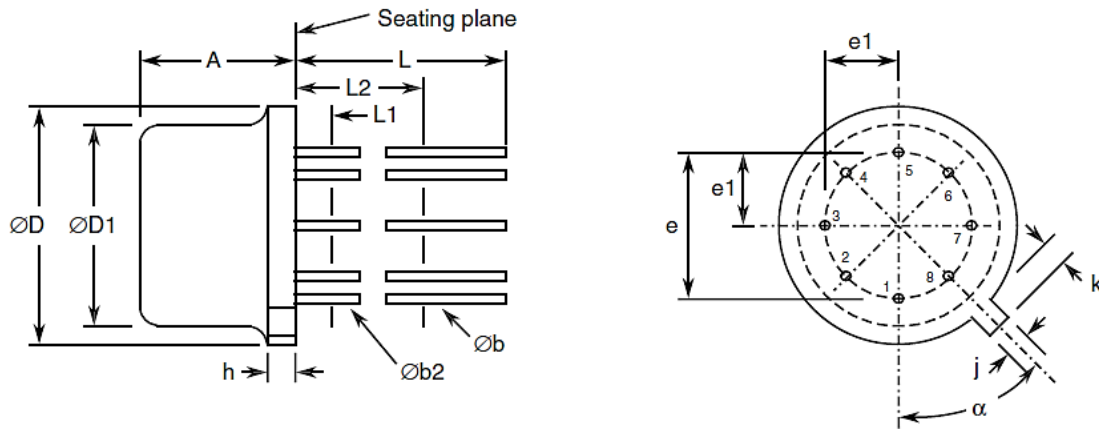
Characteristics	Symbols	Maximum Ratings	Units	Remarks
Collector-Base Voltage	V_{CBO}	-60	V	Over entire operating temperature range
Collector-Emitter Voltage	V_{CEO}	-60	V	
Emitter-Base Voltage	V_{EBO}	-5	V	
Collector Current	I_C	50	mA	Continuous
Power Dissipation (One Section) For TO-78, CCP and FP: For TO-78:	P_{totO1} P_{totO2}	0.5 0.5	W W	At $T_{amb} \leq +25^{\circ}C$ At $T_{case} \leq +25^{\circ}C$
Power Dissipation (Both Sections) For TO-78, CCP and FP: For TO-78:	P_{totB1} P_{totB2}	0.6 0.6	W W	At $T_{amb} \leq +25^{\circ}C$ At $T_{case} \leq +25^{\circ}C$
Thermal Resistance, Junction-to-Ambient	$R_{th(j-a)}$	350 291.7	$^{\circ}C/W$	For one section For both sections
Thermal Resistance, Junction-to-Case	$R_{th(j-c)}$	350 291.7	$^{\circ}C/W$	For one section For both sections Note 1
Operating Temperature Range	T_{op}	-55 to +200	$^{\circ}C$	Note 2
Storage Temperature Range	T_{stg}	-65 to +200	$^{\circ}C$	Note 2
Soldering Temperature For FP: For TO-78: For CCP:	T_{sol}	+265 +260 +245	$^{\circ}C$	Note 3 Note 3 Note 4

NOTES:

1. Thermal Resistance, Junction-to-Case only applies to TO-78 packaged Variants.
2. For Variants with tin-lead plating or hot solder dip lead finish all testing, and any handling, performed at $T_{amb} > +125^{\circ}C$ shall be carried out in a 100% inert atmosphere.
3. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.
4. Duration 5 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.

1.6 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

1.6.1 Metal Can Package (TO-78) - 6 lead

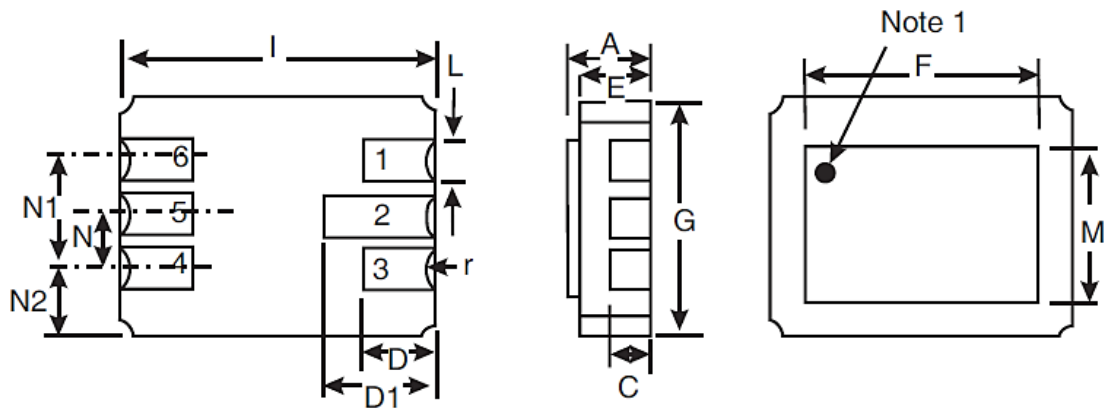


Symbols	Dimensions mm		Notes
	Min	Max	
A	4.19	4.7	
$\varnothing b$	0.406	0.533	2, 3
$\varnothing b2$	0.406	0.483	2, 3
$\varnothing D$	8.51	9.4	
$\varnothing D1$	7.75	8.51	
e	5.08 BSC		4
e1	2.54 BSC		4
h	-	1.02	
j	0.711	0.864	
k	0.737	1.14	5
L	12.7	-	2
L1	-	1.27	3
L2	6.35	-	3
a	45° BSC		1, 4, 6

NOTES:

- Terminal identification is specified by reference to the tab position where lead 1 = collector 1, lead 2 = base 1, lead 3 = emitter 1, lead 5 = emitter 2, lead 6 = base 2 and lead 7 = collector 2. Lead numbers 4 and 8 are not present on the actual package; they are shown in the drawing for information only.
- Applies to all leads.
- $\varnothing b2$ applies between $L1$ and $L2$. $\varnothing b$ applies between $L2$ and 12.7mm from the seating plane. Diameter is uncontrolled within $L1$ and beyond 12.7mm from the seating plane.
- Leads having maximum diameter 0.483mm measured in the gauging plane 1.37 (+0.025, -0) mm below the seating plane of the device shall be within 0.178mm of their true position relative to a maximum-width-tab.
- Measured from the maximum diameter of the actual device.
- Tab centreline.

1.6.2 Chip Carrier Package (CCP) - 6 terminal

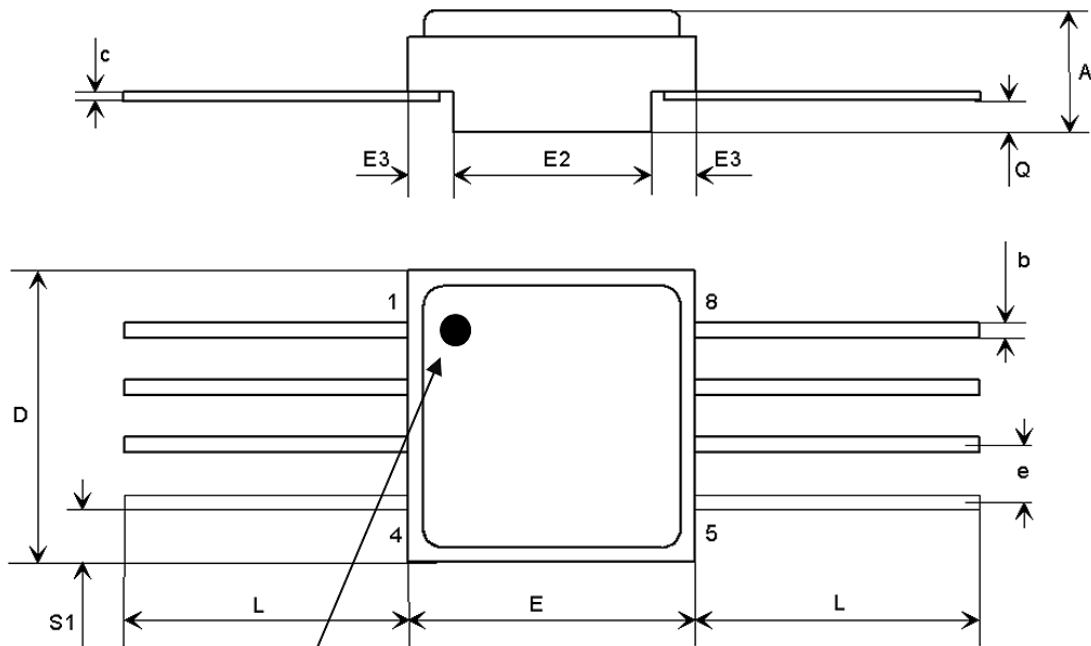


Symbols	Dimensions mm		Notes
	Min	Max	
A	1.53	1.96	
C	0.89 TYPICAL		2
D	1.52	1.78	
D1	2.08	2.49	
E	1.24	1.55	
F	5.76	5.92	
G	4.19	4.45	
I	6.1	6.35	
L	0.55	0.71	2
M	3.86	4.01	
N	1.14	1.4	
N1	2.41	2.67	
N2	0.89 TYPICAL		
r	0.23 TYPICAL		2

NOTES:

- Terminal identification is specified, when viewing the top side of the package, by reference to a black ink dot adjacent to terminal 1 = base 2. Terminal 2 = collector 2, terminal 3 = emitter 2, terminal 4 = emitter 1, terminal 5 = collector 1 and terminal 6 = base 1.
- Applies to all terminals.

1.6.3 Flat package (FP) – 8 Pin



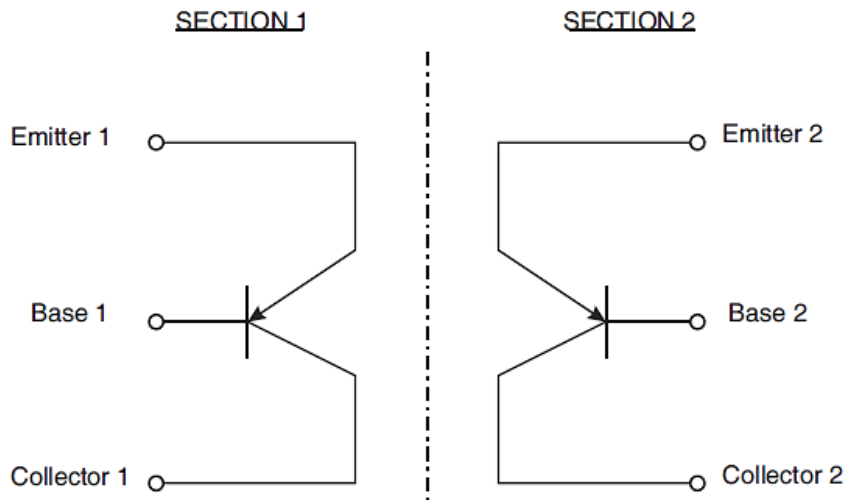
Note 1

Symbols	Dimensions mm		Notes
	Min	Max	
A	2.24	2.64	
b	0.38	0.48	2
c	0.10	0.16	2
D	6.35	6.61	
E	6.35	6.61	
E2	4.32	4.58	
E3	0.88	1.14	
e	1.27 TYPICAL		4
L	3 TYPICAL		2
Q	0.66	0.92	
S1	0.92	1.32	3

NOTES:

- Terminal identification is specified, when viewing the top side of the package, by reference to a black ink dot adjacent to terminal 1 = collector 1, terminal 2 = base 1, terminal 3 = emitter 1, terminal 6 = emitter 2 terminal 7 = base 2, terminal 8 = collector 2, terminals 4 and 5 are connected to seal ring and lid.
- Applies to all pins.
- 4 places.
- 6 places.

1.7 FUNCTIONAL DIAGRAM



NOTES:

1. For TO-78, the case is not connected to any lead.
2. For CCP, the lid is not connected to any terminal.
3. For FP, the lid is connected to terminals 4 and 5.

1.8 MATERIALS AND FINISHES

Materials and finishes shall be as follows:

- (a) Case
For the metal can package the case shall be hermetically sealed and have a metal body with hard glass seals.
For the chip carrier package and the flat package, the case shall be hermetically sealed and have a ceramic body with a Kovar lid.
- (b) Leads/Terminals
As specified in Component Type Variants.

2 REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

2.1.1 Deviations from the Generic Specification

None.

2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

- (a) Terminal identification (applies to CCP and FP packages).
- (b) The ESCC qualified components symbol (for ESCC qualified components only).
- (c) The ESCC Component Number.
- (d) Traceability information.

2.3 TERMINAL STRENGTH

The test conditions for terminal strength, tested as specified in the ESCC Generic Specification, shall be as follows:

- For TO-78, Test Condition: E, lead fatigue.
- For FP, Test Condition: E, lead fatigue. The applied weight shall be 3 ounces, with three bends of 15°.

2.4 ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES

Electrical measurements shall be performed at room, high and low temperatures.

2.4.1 Room Temperature Electrical Measurements

The measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}C$.

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	3001	$I_C = -10\mu A$, Bias condition D	-60	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	3011	$I_C = -10mA$, Bias condition D, Note 1	-60	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	3026	$I_E = -10\mu A$, Bias condition D	-5	-	V
Collector-Base Cut-off Current	I_{CBO}	3036	$V_{CB} = -50V$, Bias condition D	-	-10	nA
Emitter-Base Cut-off Current	I_{EBO}	3061	$V_{EB} = -4V$, Bias condition D	-	-20	nA
Collector-Emitter Saturation Voltage	$V_{CE(sat)1}$	3071	$I_C = -100\mu A$ $I_B = -10\mu A$ Note 1	-	-200	mV
	$V_{CE(sat)2}$	3071	$I_C = -1mA$ $I_B = -100\mu A$ Note 1	-	-250	mV
Base-Emitter Saturation Voltage	$V_{BE(sat)1}$	3066	$I_C = -100\mu A$ $I_B = -10\mu A$ Test Condition A Note 1	-	-700	mV
	$V_{BE(sat)2}$	3066	$I_C = -1mA$ $I_B = -100\mu A$ Test Condition A Note 1	-	-800	mV

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Forward-Current Transfer Ratio	h_{FE1}	3076	$V_{CE} = -5V; I_C = -10\mu A$	100	-	-
	h_{FE2}	3076	$V_{CE} = -5V; I_C = -100\mu A$	150	450	-
	h_{FE3}	3076	$V_{CE} = -5V; I_C = -500\mu A$	150	450	-
	h_{FE4}	3076	$V_{CE} = -5V; I_C = -1mA$	150	450	-
	h_{FE5}	3076	$V_{CE} = -5V; I_C = -10mA$	125	-	-
Forward-Current Transfer Ratio Comparison	$h_{FE2-1}/$ h_{FE2-2}	3076	$V_{CE} = -5V; I_C = -100\mu A$	0.9	1.1	-
Base-Emitter Voltage Differential	$ V_{BE1}-V_{BE2} 1$	3066	$I_C = -10\mu A$ $V_{CE} = -5V$ Test Condition B Note 2	-	5	mV
	$ V_{BE1}-V_{BE2} 2$	3066	$I_C = -100\mu A$ $V_{CE} = -5V$ Test Condition B Note 2	-	3	mV
	$ V_{BE1}-V_{BE2} 3$	3066	$I_C = -10mA$ $V_{CE} = -5V$ Test Condition B Note 2	-	5	mV
Leakage Current Between Sections	$I_{LS(e-e)}$	-	-50V to Emitter 2 0V to Emitter 1	-	5	μA
	$I_{LS(b-b)}$	-	-50V to Base 2 0V to Base 1	-	5	μA
	$I_{LS(c-c)}$	-	-50V to Collector 2 0V to Collector 1	-	5	μA
Current Gain Bandwidth Product	f_T	3206	$V_{CE} = -5V,$ $I_C = -1mA$ $f = 100MHz$ Note 3	80	500	MHz
Small-Signal Short- Circuit Forward-Current Transfer Ratio	h_{fe}	3206	$I_C = -1mA, V_{CE} = -10V$ $f = 1kHz$ Note 3	150	600	-
Spot Noise Figure	NF1	3246	$V_{CE} = -5V$ $I_C = -200\mu A$ $R_s = 2k\Omega$ $f = 100Hz$ BW = 20Hz Note 3	-	7	dB
	NF2	3246	$V_{CE} = -5V$ $I_C = -200\mu A$ $R_s = 2kW$ $f = 1kHz$ BW = 200Hz Note 3	-	3	dB

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Wide-Band Noise Figure	NF _w	3246	V _{CE} = -5V I _C = -200μA R _s = 2kΩ 10Hz ≤ f ≤ 15.7kHz Note 3	-	3.5	dB
Output Capacitance	C _{obo}	3236	V _{CB} = -5V, I _E = 0A 100kHz ≤ f ≤ 1MHz Note 3	-	6	pF
Input Capacitance	C _{ibo}	3240	V _{EB} = -500mV, I _C = 0A 100kHz ≤ f ≤ 1MHz Note 3	-	15	pF
Small-Signal Input Impedance	h _{ie}	3201	V _{CE} = -10V I _C = -1mA f = 1kHz Note 3	3	30	kΩ

NOTES:

1. Pulsed measurement: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
2. Any device whose measurement values exceed the specified limits shall be removed from the lot, but only count for PDA when such values exceed twice the specified limits (i.e. > 10mV or > 6mV).
3. For AC characteristics read and record measurements shall be performed on a sample of 32 components with 0 failures allowed. Alternatively a 100% inspection may be performed.

2.4.2 High and Low Temperatures Electrical Measurements

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Collector-Base Cut-off Current	I _{CBO}	3036	T _{amb} = +150 (+0 -5)°C V _{CB} = -50V, Bias Condition D	-	-10	μA
Forward-Current Transfer Ratio 2	h _{FE2}	3076	T _{amb} = -55 (+5 -0)°C V _{CE} = -5V I _C = -100μA	60	-	-
Forward-Current Transfer Ratio Comparison	h _{FE2-1} / h _{FE2-2}	3076	T _{amb} = -55 to +125°C V _{CE} = -5V, I _C = -100μA	0.85	1.18	-
Base-Emitter Voltage Differential Change	Δ(V _{BE1} - V _{BE2})ΔT _{amb} 1	3066	T _{amb} = -55 (+5 -0)°C to +25 ±3°C V _{CE} = -5V I _C = -100μA Test condition B	-	800	mV
	Δ(V _{BE1} - V _{BE2})ΔT _{amb} 2	3066	T _{amb} = +25 ±3°C to +125 (+0 -5) °C V _{CE} = -5V I _C = -100μA Test condition B	-	1000	mV

NOTES:

1. Read and record measurements shall be performed on a sample of 5 components with 0 failures allowed. Alternatively a 100% inspection may be performed.

2.5 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}\text{C}$.

The test methods and test conditions shall be as per the corresponding test defined in Para. 2.4.1 Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits			Units
		Drift Value Δ	Absolute		
			Min	Max	
Collector-Base Cut-off Current	I_{CBO}	± 2 or (1) $\pm 100\%$	-	-10	nA
Collector-Emitter Saturation Voltage 2	$V_{CE(sat)2}$	± 15 or (1) $\pm 10\%$	-	-250	mV
Forward-Current Transfer Ratio 2	h_{FE2}	$\pm 15\%$	150	450	-

NOTES:

1. Whichever is the greater referred to the initial value.

2.6 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3^{\circ}\text{C}$.

The test methods and test conditions shall be as per the corresponding test defined in either Para. 2.4.1 Room Temperature Electrical Measurements or Para. 2.4.2 High and Low Temperatures Electrical Measurements, as applicable.

The limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits		Units
		Min	Max	
Collector-Base Cut-off Current	I_{CBO}	-	-20	nA
Collector-Emitter Saturation Voltage 2	$V_{CE(sat)2}$	-	-250	mV
Forward-Current Transfer Ratio 2	h_{FE2}	150	450	-
Forward-Current Transfer Ratio Comparison	h_{FE2-1}/h_{FE2-2}	0.85	1.18	-

Characteristics	Symbols	Limits		Units
		Min	Max	
Base-Emitter Voltage Differential 2	$ V_{BE1}-V_{BE2} 2$	-	6	mV
Base-Emitter Voltage Differential Change (Note 1)	$ \Delta(V_{BE1}-V_{BE2})\Delta T_{amb} 1$	-	1	mV
	$ \Delta(V_{BE1}-V_{BE2})\Delta T_{amb} 2$	-	1.2	mV

NOTES:

1. Measured after Operating Life test only.

2.7 **HIGH TEMPERATURE REVERSE BIAS BURN-IN CONDITIONS**

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+150 (+0 -5)	°C
Collector-Base Voltage (Note 1)	V_{CB}	-45	V
Duration	t	72 Minimum	hrs

NOTES:

1. On completion of High Temperature Reverse Bias Burn-in, the collector-base voltage shall continue to be applied until $T_{case} < +30^{\circ}C$.

2.8 **POWER BURN-IN CONDITIONS**

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+25 to +50	°C
Power Dissipation (Both Sections)	P_{totB}	As per Maximum Ratings. Derate P_{totB1} at the chosen T_{amb} using the specified $R_{th(j-a)}$.	W
Collector-Base Voltage	V_{CB}	-45	V

2.9 **OPERATING LIFE CONDITIONS**

The conditions shall be as specified for Power Burn-in in Para. 2.8.

2.10 **TOTAL DOSE RADIATION TESTING**

All lots shall be irradiated in accordance with ESCC Basic Specification No. 22900, low dose rate (window 2: 36 to 360rad/h).

2.10.1 Bias Conditions and Total Dose Level for Total dose Radiation Testing

The following bias conditions shall be used for Total Dose Radiation Testing:

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T _{amb}	+20 ±5	°C
Bias Condition 1: Collector-Emitter Voltage	V _{CES}	≥ 80% V _{(BR)CEO}	V
Bias Condition 2: Collector-Emitter Voltage	V _{CES}	0	V

The total dose level applied shall be as specified in the component type variant information herein or in the Purchase Order.

2.10.2 Electrical Measurements for Radiation Testing

Prior to irradiation testing the devices shall have successfully met Para. 2.4.1 Room Temperature Electrical Measurements specified herein.

Unless otherwise stated the measurements shall be performed at T_{amb} = +22 ±3°C.

Unless otherwise specified the test methods and test conditions shall be as per the corresponding test defined in Para. 2.4.1 Room Temperature Electrical Measurements.

The parameters to be measured during and on completion of irradiation testing are shown below.

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Collector-Base Breakdown Voltage	V _{(BR)CBO}	Para. 2.4.1	Para. 2.4.1	-60	-	V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	Para. 2.4.1	Para. 2.4.1	-60	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	Para. 2.4.1	Para. 2.4.1	-5	-	V
Collector-Base Cut-off Current	I _{CBO}	Para. 2.4.1	Para. 2.4.1	-	-10	nA
Emitter-Base Cut-off Current	I _{EBO}	Para. 2.4.1	Para. 2.4.1	-	-20	nA
Collector-Emitter Saturation Voltage	V _{CE(sat)1}	Para. 2.4.1	Para. 2.4.1	-	-200	mV
	V _{CE(sat)2}			-	-250	mV
Base-Emitter Saturation Voltage	V _{BE(sat)1}	Para. 2.4.1	Para. 2.4.1	-	-700	mV
	V _{BE(sat)2}			-	-800	mV
Forward-Current Transfer Ratio (post irradiation gain calculation) (Note 1)	[h _{FE1}]	3076	V _{CE} = -5V, I _C = -10µA	[50]	-	-
	[h _{FE2}]		V _{CE} = -5V, I _C = -100µA	[75]	450	-
	[h _{FE3}]		V _{CE} = -5V, I _C = -500µA	[75]	450	-
	[h _{FE4}]		V _{CE} = -5V, I _C = -1mA	[75]	450	-
	[h _{FE5}]		V _{CE} = -5V, I _C = -10mA	[65]	-	-

NOTES:

1. The post-irradiation gain calculation of $[h_{FE}]$, made using h_{FE} measurements from prior to and on completion of irradiation testing and after each annealing step if any, shall be as specified in [MIL-STD-750 Method 1019](#).

APPENDIX 'A'
AGREED DEVIATIONS FOR STMICROELECTRONICS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Para. 2.1.1, Deviations from the Generic Specification: Production Control - Chart F2	Special In-Process Controls - Internal Visual Inspection. For CCP packages the criteria specified for voids in the fillet and minimum die mounting material around the visible die perimeter for die mounting defects may be omitted providing that a radiographic inspection to verify the die-attach process is performed on a sample basis in accordance with STMicroelectronics procedure 0076637.
Para. 2.1.1, Deviations from the Generic Specification: Screening Tests - Chart F3	Solderability is not applicable unless specifically stipulated in the Purchase Order.
Para. 2.4.1, Room Temperature Electrical Measurements	All AC characteristics (Para. 2.4.1 Note 3) may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes AC characteristic measurements per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order.
Para. 2.4.2, High and Low Temperatures Electrical Measurements	All characteristics specified may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes characteristic measurements at high and low temperatures per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order.